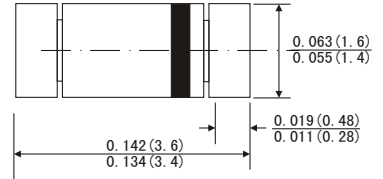


FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily Intended for high level UHF/VHF detection and pulse applications with broad dynamic range
- The diode is also available in the DO-35 case with type designation BAT19,
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MiniMELF



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: MiniMELF glass case(SOD-80)
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.05 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V_{RRM}	10	V
Forward Continuous Current	I_F	30	mA
Surge non repetitive Forward current $t_p \leq 1s$	I_{FSM}	2.0	A
Storage temperature range	T_{STG}	-55 to+150	°C
Junction temperature	T_J	125	°C

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse brekover voltage at $I_R=10\mu A$	V_R	10			V V
Leakage current at $V_R=5V$	I_R			100	nA
Forward voltage drop at $I_F=1mA$ Test pulse: $t_p \leq 300\mu s$ $\delta < 2\%$ $I_F=20mA$	V_F V_F			0.40 1.0	V V
Junction Capacitance at $V_R=0V$, $f=1GHz$	C_J			1.2	pF
Thermal resistance	$R_{\theta JA}$			400	K/W

RATINGS AND CHARACTERISTICS CURVES LL19

Figure 1. Forward current versus forward voltage at low level (typical values)

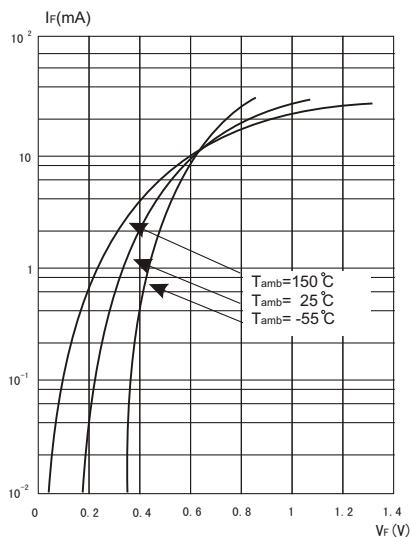


Figure 2. Capacitance C_J versus reverse applied voltage V_R (typical values)

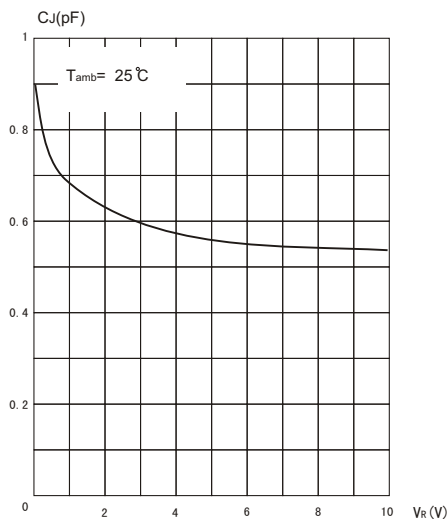


Figure 3. Reverse current versus ambient temperatures

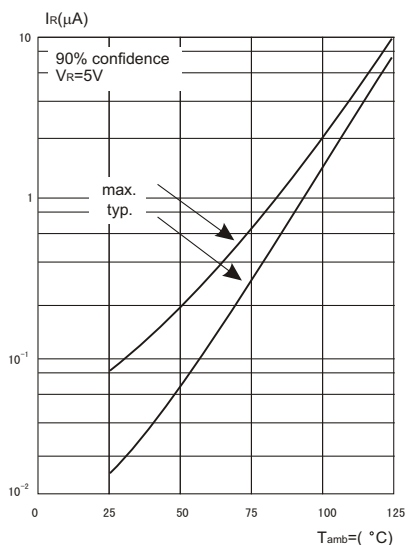


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

